NPN Silicon Epitaxial Planar Transistor

Audio frequency low noise amplifier.

The transistor is subdivided into four groups, P, F, E and U according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base TO-92 Plastic Package Weight approx. 0.19g

Absolute Maximum Ratings (T_a = 25 °C)

| | Symbol | Value | Unit |
|---------------------------|------------------|-------------|------|
| Collector Base Voltage | V _{CBO} | 120 | V |
| Collector Emitter Voltage | V _{CEO} | 120 | V |
| Emitter Base Voltage | V _{EBO} | 5 | V |
| Collector Current | I _C | 50 | mA |
| Base Current | I _B | 10 | mA |
| Power Dissipation | P _{tot} | 300 | mW |
| Junction Temperature | T _j | 150 | °C |
| Storage Temperature Range | Ts | -55 to +150 | °C |









Characteristics at T_{amb}=25 °C

| | Symbol | Min. | Тур. | Max. | Unit |
|---|----------------------|------|------|------|------|
| DC Current Gain | | | | | |
| at V _{CE} =6V, I _C =1mA | | | | | |
| Current Gain Group F | h _{FE} | 200 | - | 400 | - |
| F | h _{FE} | 300 | - | 600 | - |
| E | h _{FE} | 400 | - | 800 | - |
| ι | J h _{FE} | 600 | - | 1200 | - |
| at V _{CE} =6V, I _C =0.1mA | h _{FE} | 150 | 580 | - | - |
| Collector Cutoff Current | | | | | |
| at V _{CB} =120V | I _{CBO} | - | - | 0.05 | μΑ |
| Emitter Cutoff Current | | | | | |
| at V _{EB} =5V | I _{EBO} | - | - | 0.05 | μΑ |
| Collector Cutoff Current | | | | | |
| at V _{CE} =100V | I _{CEO} | - | - | 1 | μΑ |
| Gain Bandwidth Product | | | | | |
| at V _{CE} =6V, I _E =1mA | f _T | 50 | 110 | - | MHz |
| Noise Voltage | NV | - | 25 | 40 | mV |
| Output Capacitance | | | | | |
| at V _{CB} =30V, f=1MHz | Сов | - | 1.6 | 2.5 | pF |
| Base Emitter Voltage | | | | | |
| at V _{CE} =6V, I _C =1mA | V_{BE} | 0.55 | 0.59 | 0.65 | V |
| Collector Saturation Voltage | | | | | |
| at $I_C=10$ mA, $I_B=1$ mA | V _{CE(sat)} | - | 0.07 | 0.3 | V |









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